# General Purpose Transistors NPN Silicon

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-416/SC-75 package which is designed for low power surface mount applications.

#### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*



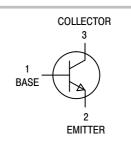
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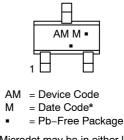
## GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



SOT-416/SC-75 CASE 463 STYLE 1



#### MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT3904TT1G	SOT-416 (Pb-Free)	3,000 Tape & Reel
SMMBT3904TT1G	SOT-416 (Pb-Free)	3,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	۱ <sub>C</sub>	200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR–4 Board (Note 1) @T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	600	°C/W
Total Device Dissipation, FR–4 Board (Note 2) @T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please

download the ON Semiconductor Soldering and Mounting Techniques

1. FR-4 @ Minimum Pad

2. FR-4 @ 1.0 × 1.0 Inch Pad

Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	V <sub>(BR)CEO</sub>	40	-	Vdc
Collector – Base Breakdown Voltage $(I_{C} = 10 \ \mu Adc, I_{E} = 0)$	V <sub>(BR)CBO</sub>	60	_	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \ \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	_	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 3)			•	*
	h <sub>FE</sub>	40 70 100 60 30	_  300  _	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	- -	0.2 0.3	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	0.65 _	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	fT	300	-	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	_	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	_	8.0	pF
Input Impedance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0	10	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.5	8.0	X 10 <sup>-4</sup>
Small – Signal Current Gain (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 1.0 mAdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 100 μAdc, R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz)	NF	-	5.0	dB
SWITCHING CHARACTERISTICS				
Delay Time (V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = -0.5 Vdc) MMBT3904TT1G, SMMBT3904TT1G	t <sub>d</sub>	-	35	

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = -0.5 Vdc) MMBT3904TT1G, SMMBT3904TT1G	t <sub>d</sub>	-	35		
Rise Time	(I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc) MMBT3904TT1G, SMMBT3904TT1G	t <sub>r</sub>	_	35	ns	
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc) MMBT3904TT1G, SMMBT3904TT1G		_	200	115	
Fall Time	(I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc) MMBT3904TT1G, SMMBT3904TT1G	t <sub>f</sub>	_	50		

3. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

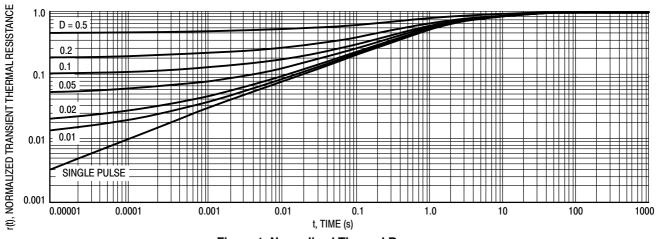
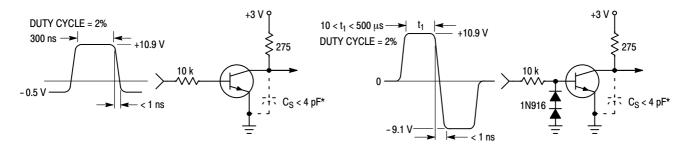
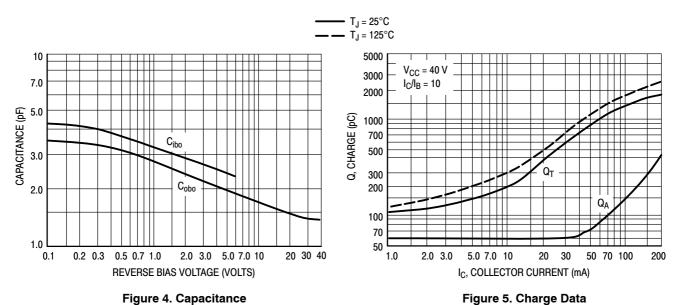


Figure 1. Normalized Thermal Response

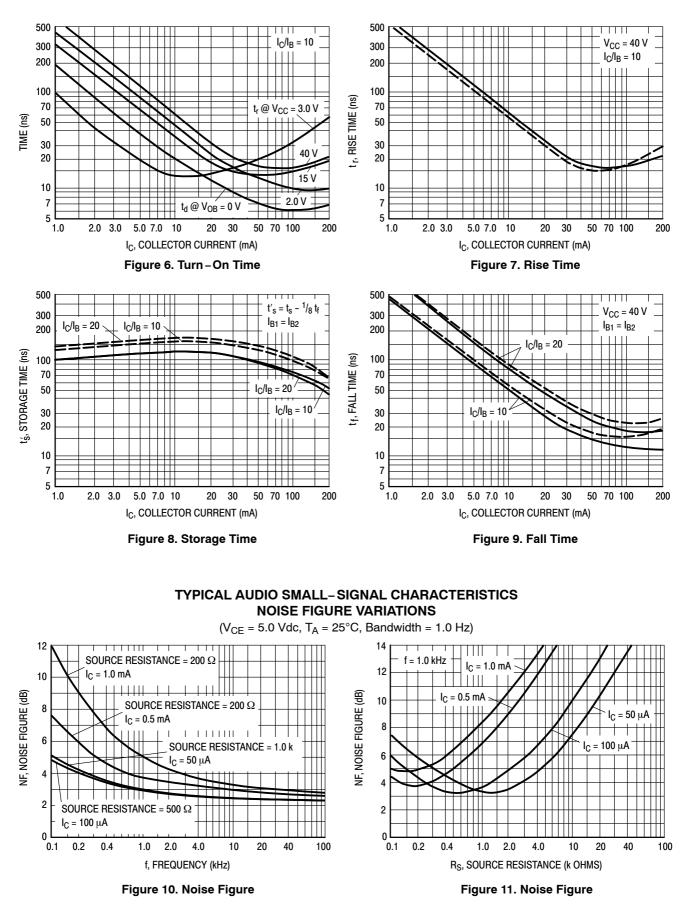


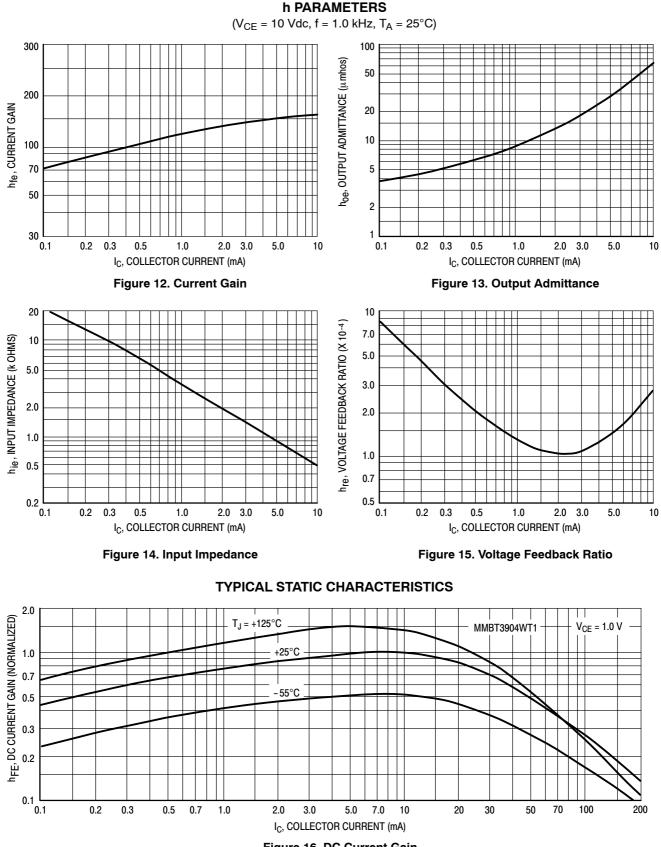
\* Total shunt capacitance of test jig and connectors

Figure 2. Delay and Rise Time Equivalent Test Circuit Figure 3. Storage and Fall Time Equivalent Test Circuit

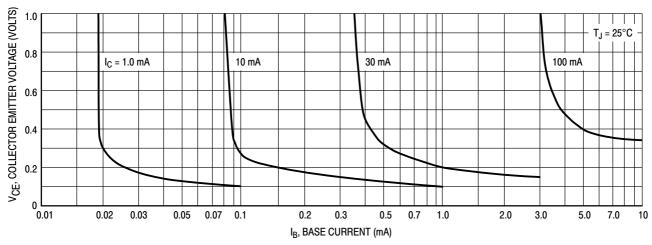


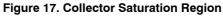
## **TYPICAL TRANSIENT CHARACTERISTICS**

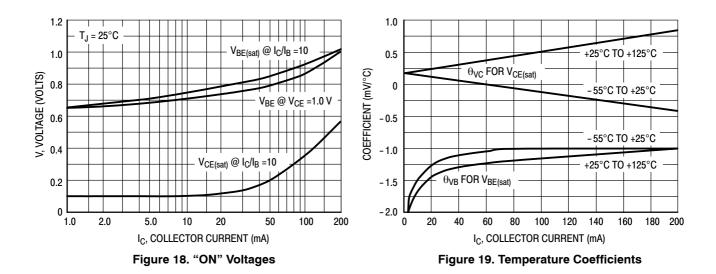




#### Figure 16. DC Current Gain

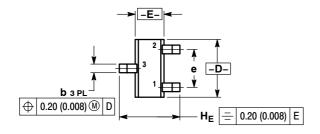


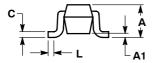




#### PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463-01 ISSUE F





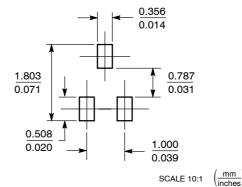
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			C	.04 BSC	
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR





\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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